

Title (en)

METHOD FOR DEPOSITING POLYCRYSTALLINE SILICONE

Title (de)

VERFAHREN ZUR ABSCHIEDUNG VON POLYKRISTALLINEM SILICIUM

Title (fr)

PROCÉDÉ POUR DÉPOSER DU SILICIUM POLYCRISTALLIN

Publication

**EP 2945908 A1 20151125 (DE)**

Application

**EP 14700836 A 20140113**

Priority

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Abstract (en)

[origin: WO2014111326A1] The invention relates to a method for separating polycrystalline silicone, comprising passing of a reaction gas comprising a silicon-containing component and hydrogen into a reactor, whereby polycrystalline silicon in the form of rods is deposited, characterized in that upon completion of the deposition the reactor is opened and ventilated for a specific time.

IPC 8 full level

**C01B 33/035** (2006.01)

CPC (source: EP US)

**C01B 33/035** (2013.01 - EP US); **H01L 21/02532** (2013.01 - US); **H01L 21/02595** (2013.01 - US); **H01L 21/0262** (2013.01 - US)

Citation (search report)

See references of WO 2014111326A1

Citation (examination)

EP 2105409 A1 20090930 - MITSUBISHI MATERIALS CORP [JP]

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Designated extension state (EPC)

BA ME

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